

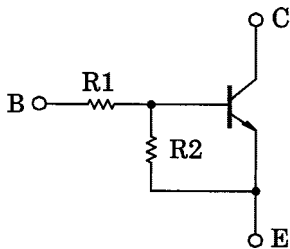
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN1007, RN1008, RN1009

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2007~RN2009

Equivalent Circuit And Bias Resister Values

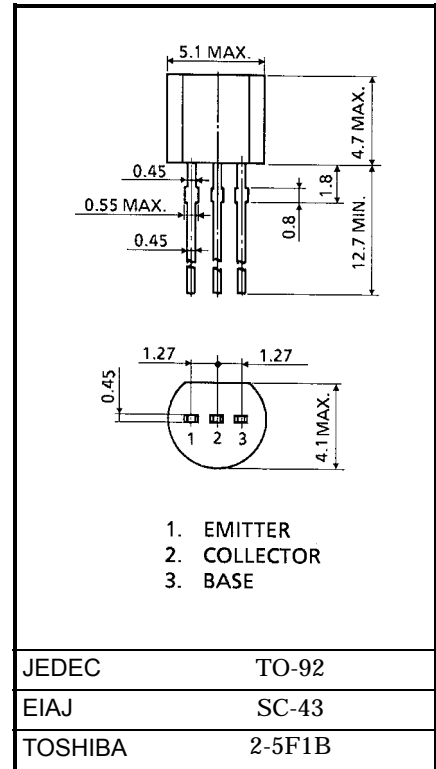


Type No.	R1 (kΩ)	R2 (kΩ)
RN1007	10	47
RN1008	22	47
RN1009	47	22

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	RN1007	6
		RN1008	7
		RN1009	15
Collector current	I_C	100	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Unit in mm



Weight: 0.21g

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Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	—	$V_{CB} = 50V, I_E = 0$	—	—	100	nA
		I_{CEO}		$V_{CE} = 50V, I_B = 0$	—	—	500	
Emitter cut-off current	RN1007	I_{EBO}	—	$V_{EB} = 6V, I_C = 0$	0.081	—	0.15	mA
	RN1008			$V_{EB} = 7V, I_C = 0$	0.078	—	0.145	
	RN1009			$V_{EB} = 15V, I_C = 0$	0.167	—	0.311	
DC current gain	RN1007	h_{FE}	—	$V_{CE} = 5V, I_C = 10mA$	80	—	—	
	RN1008				80	—	—	
	RN1009				70	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)}$	—	$I_C = 5mA, I_B = 0.25mA$	—	0.1	0.3	V
Input voltage (ON)	RN1007	$V_{I(ON)}$	—	$V_{CE} = 0.2V, I_C = 5mA$	0.7	—	1.8	V
	RN1008				1.0	—	2.6	
	RN1009				2.2	—	5.8	
Input voltage (OFF)	RN1007	$V_{I(OFF)}$	—	$V_{CE} = 5V, I_C = 0.1mA$	0.5	—	1.0	V
	RN1008				0.6	—	1.16	
	RN1009				1.5	—	2.6	
Transition frequency		f_T	—	$V_{CE} = 10V, I_C = 5mA$	—	250	—	MHz
Collector Output capacitance		C_{ob}	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3	6	pF
Input resistor	RN1007	R1	—		7	10	13	kΩ
	RN1008				15.4	22	28.6	
	RN1009				32.9	47	61.1	
Resistor ratio	RN1007	R1/R2	—		0.191	0.213	0.232	—
	RN1008				0.421	0.468	0.515	
	RN1009				1.92	2.14	2.35	

